TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK3077A

#### VHF/UHF Band Amplifier Applications

Unit: mm

• Output power:  $P_0 \ge 20.5 dBmW$ 

• Gain:  $G_p \ge 10.5 dB$ 

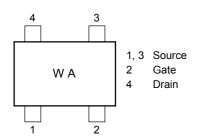
• Drain Efficiency:  $\eta D \ge 50\%$ 

#### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	10	V
Gate-source voltage	$V_{GSS}$	5	V
Drain current	I <sub>D</sub>	0.1	Α
Power dissipation	$P_{D}$	0.1	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-45~150	°C

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#### Marking



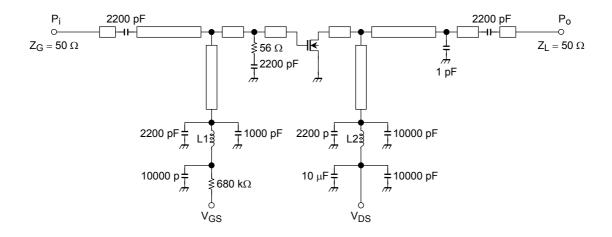
### Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output power	PO	V <sub>DS</sub> = 4.5 V, lidle = 20 mA	20.5	_	_	dBmW
Drain efficiency	η <sub>D</sub>	(V <sub>GS</sub> = adjust)	50	_	_	%
Power gain	G <sub>P</sub>	f = 470 MHz, P <sub>i</sub> = 10dBmW	10.5	_	_	dB
Threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 4.8 V, I <sub>D</sub> = 0.5 mA	0.25	_	1.25	V
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V	_	_	10	μA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = 5 V, V <sub>DS</sub> = 0 V	_	_	5	μA
Load mismatch (Note 1	) —	$V_{DS}$ = 6.5 V, f = 470 MHz, $P_i$ = 10dBmW, $P_0$ = 20.5dBmW ( $V_{GS}$ = adjust) VSWR LOAD 10:1 all phase	No degradation		_	

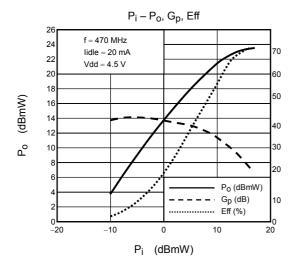
Caution: This transistor is the electrostatic sensitive device. Please handle with caution.

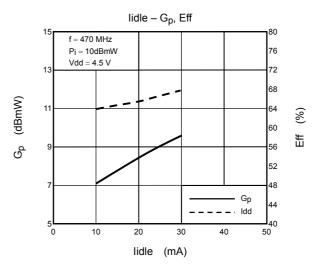
Note 1: When the RF output power test fixture is used

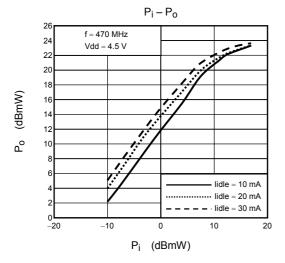
## **PF Output Power Test Fixture**

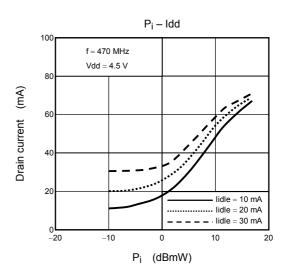


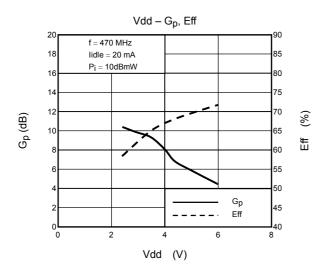
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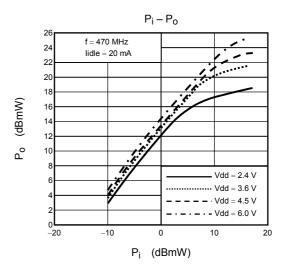




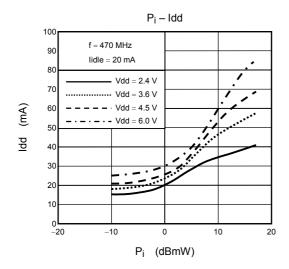








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Caution: These are typical curves and devices are not necessarily guaranteed at these curves.

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